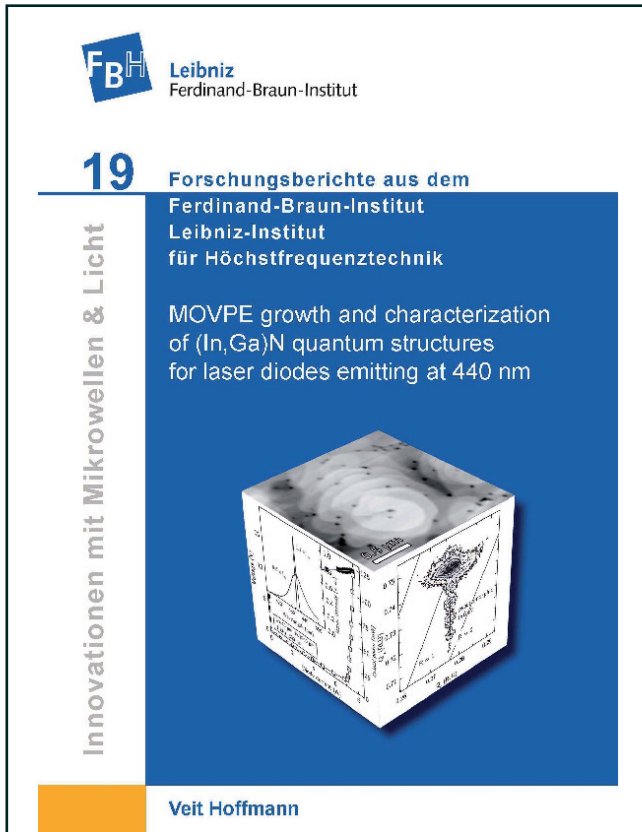




Veit Hoffmann (Autor)

MOVPE growth and characterization of (In,Ga)N quantum structures for laser diodes emitting at 440 nm



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